

Docket No. 8733.154.00



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3/13/01

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Jin JANG et al.

GAU: 1765

SERIAL NO: 09/350,313

EXAMINER: R. KUNEMUND

FILING DATE: JULY 9, 1999

FOR: METHOD OF CRYSTALLIZING AMORPHOUS SILICON LAYER AND  
CRYSTALLIZING APPARATUS THEREOF

**AMENDMENT**

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated September 12, 2000, please amend the above-  
identified application as follows:

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**IN THE CLAIMS:**

Please amend the claims as follows:

1. (Amended) A method of crystallizing amorphous silicon, comprising:  
depositing an inducing substance for silicon crystallization on an exposed surface of an  
amorphous silicon layer by plasma exposure; and  
annealing the amorphous silicon layer.
2. (Amended) A method of crystallizing amorphous silicon, comprising:  
providing a substrate on which an amorphous silicon layer is formed;  
depositing an inducing substance for silicon crystallization on an exposed surface of an  
amorphous silicon layer by plasma exposure; and